A2 cont'd

layers 31 and 41. The semiconductor layer of Nos. 1-4 in the bottom reflection layer 21 is layered 40 times, the semiconductor layer of No. 9-10 in the active layer 23 is layered twice, and the dielectric layer of Nos. 22-23 in the dielectric reflection layers 31 and 41 is layered 7 times. No. 21 in the intermediate layer 25 shows the cap layer 26.

Page 9, delete the third paragraph and insert:

A3

By the way, as can be seen in Table 1, φ_b, σ, and a part of φ_a excluding the part that is determined by the dielectric reflection layer 31 and 41 are already defined with respect to the bottom reflection layer 21, the active layer 23 and the intermediate layer 25 that are applied commonly to all surface-emitting lasers constituting multiple wavelength surface-emitting laser devices that are manufactured by MOCVD and/or MBE processes. Thus if the phase φ_a of the light reflected by the dielectric reflection layer 31 or 41 which occupies the larger part of the role of the top reflection layer changes, then the resonance condition changes. Here, since the phase φ_a of the light reflected by the dielectric reflection layer 31 or 41 changes depending on the thickness of a plurality of dielectric layers, the change in the total thickness of the composite dielectric layer makes the resonance wavelength change.

Page 12, delete the first paragraph and insert:

A4

According to the present invention as described above, the resonance wavelength is controlled by adjusting the thickness of the dielectric layer, and thus a multiple wavelength surface-emitting laser device that emits light of a desired wavelength from each of a plurality of surface-emitting lasers can be manufactured in a continuous process, which is simple and has high reliability.